

Pseudo SRAM

Part No.	W966D6HBG	
Datasheet		
Description	This is a 64M bit CellularRAM™ compliant products, organized as 4M word by 16 bite; high-speed, CMOS pseudo-static random access memories developed for low-power, portable applications.	
Features	Supports asynchronous and burst operations VCC, VCCQ Voltages:1.7V–1.95V VCC, 1.7V–1.95V VCCQ Random access time: 70ns Burst mode READ and WRITE access: 4, 8, 16, or 32 words, or continuous burst Burst wrap or sequential Max clock rate: 133 MHz (tCLK = 7.5ns) tACLK: 5.5ns at 133 MHz, 7ns at 104 MHz Low-power features: TCR, PAR, DPD Page mode READ access:Sixteen-word page size Interpage READ access: 70ns, Intrapage READ access: 20ns	
Diagram	N/A	
Package	54VFBGA(6X8X1.0mm), RoHS compliant	
Other Files	IBIS Model	N/A
	Spice Model	N/A
	Verilog Model	N/A
Development Tools	N/A	
Others	N/A	

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